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80V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _C = +25°C
80V	16mΩ @ V _{GS} = 10V	50A
	21mΩ @ V _{GS} = 4.5V	43A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Synchronous Rectifier
- Backlighting
- Power Management Functions
- DC-DC Converters

Features

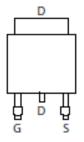
- Rated to +175°C ideal for high ambient temperature environments
- Low R_{DS(ON)} ensures on state losses are minimized
- High Conversion Efficiency
- Low Input Capacitance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

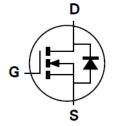
- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.33 grams (Approximate)







Pin Out Top View



Equivalent Circuit

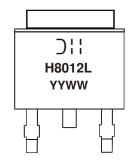
Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH8012LK3-13	TO252	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



D:: =Manufacturer's Marking
H8012L = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 14 = 2014)
WW = Week Code (01 to 53)



$\hline \textbf{Maximum Ratings} \ (@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

Characteristic	Symbol	Value	Units	
Drain-Source Voltage		V_{DSS}	80	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I _D	50 35	А
Maximum Continuous Body Diode Forward Current (Note 5)	I _S	3	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	80	Α	
Avalanche Energy, L = 60mH	E _{AS}	147	mJ	

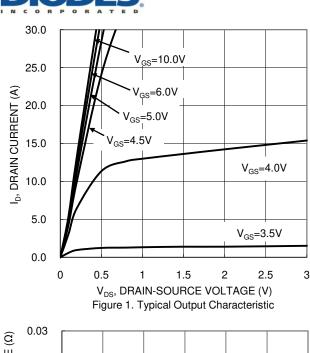
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

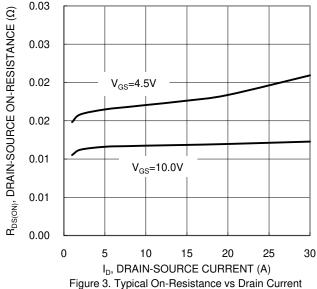
Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	2.6	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	47	°C/W
Total Power Dissipation (Note 6)	P _D	60	W
Thermal Resistance, Junction to Case (Note 6)	R _{eJC}	2.5	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	80	-	-	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μΑ	$V_{DS} = 64V$, $V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1	1.3	3	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	D	-	12.1	16	mΩ	$V_{GS} = 10V, I_D = 12A$	
Static Drain-Source Off-Nesistance	R _{DS(ON)}	-	14.8	21		$V_{GS} = 4.5V, I_D = 6A$	
Diode Forward Voltage	V_{SD}	-	0.9	1.2	٧	$V_{GS} = 0V, I_S = 25A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	-	1949	-		$V_{DS} = 40V$, $V_{GS} = 0V$, $f = 1MHz$	
Output Capacitance	Coss	-	177	-	pF		
Reverse Transfer Capacitance	C_{rss}	-	10	-			
Gate Resistance	R_g	-	0.7	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	-	15	-			
Total Gate Charge (V _{GS} = 10V)	Q_g	-	34	-	nC	V _{DS} = 40V. I _D = 12A	
Gate-Source Charge	Q_{gs}	-	6	-	110	VDS = 40V, ID = 12A	
Gate-Drain Charge	Q_{gd}	-	4.5	-			
Turn-On Delay Time	t _{D(ON)}	-	4.9	-		$V_{DD} = 40V, V_{GS} = 10V,$ $I_{D} = 12A, R_{G} = 1.6\Omega$	
Turn-On Rise Time	t _R	-	3.8	-	ns		
Turn-Off Delay Time	t _{D(OFF)}	-	16.5	-	115		
Turn-Off Fall Time	t _F	-	3.5	-			
Body Diode Reverse Recovery Time	t _{RR}	-	30.2	-	ns I 100 di/dt 1000///cc		
Body Diode Reverse Recovery Charge	Q _{rr}	-	34.6	-	nC	I _F = 12A, di/dt = 100A/μs	

- Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Device mounted on infinite heat sink and measured by thermal couple attached on bottom heat sink of package.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.





and Gate Voltage

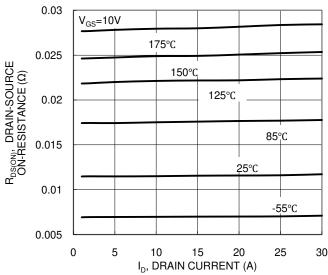
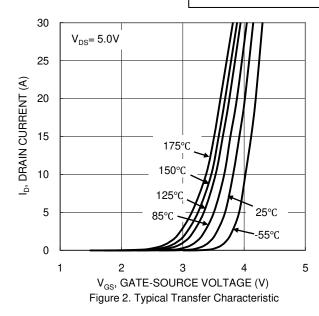
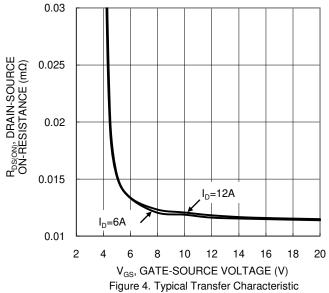


Figure 5. Typical On-Resistance vs Drain Current and Temperature





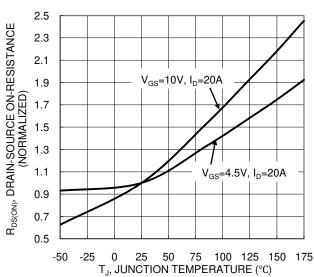
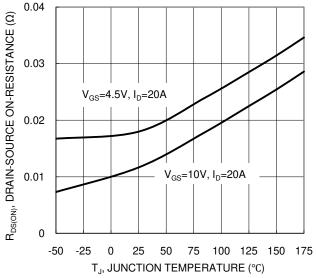
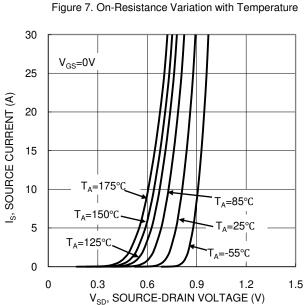
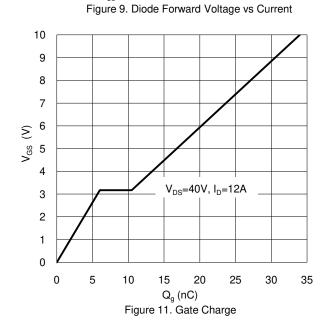


Figure 6. On-Resistance Variation with Temperature









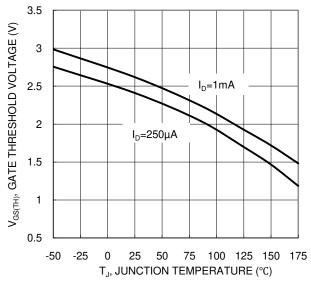
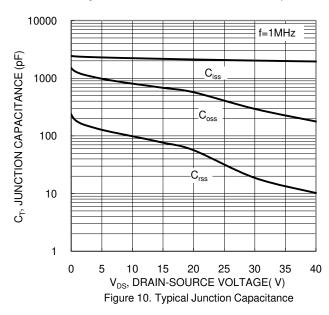
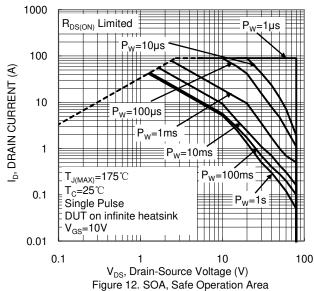


Figure 8. Gate Threshold Variation vs Temperature







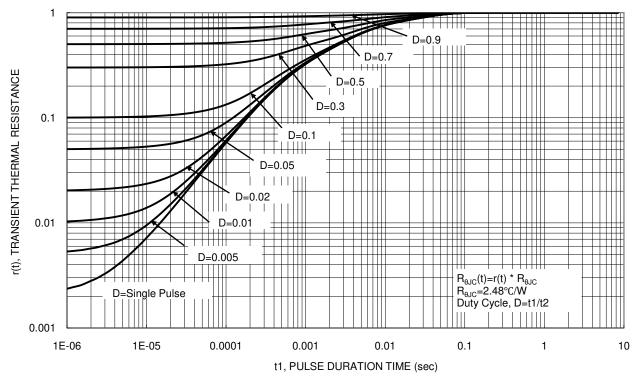
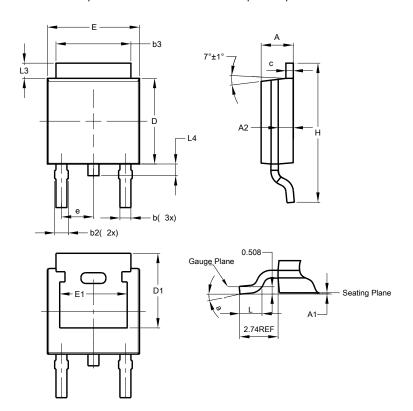


Figure 13. Transient Thermal Resistance



Package Outline Dimensions

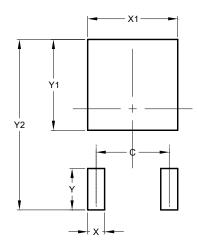
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	TO252 (DPAK)					
Dim	Min	Max	Тур			
Α	2.19	2.39	2.29			
A 1	0.00	0.13	0.08			
A2	0.97	1.17	1.07			
b	0.64	0.88	0.783			
b2	0.76	1.14	0.95			
b3	5.21	5.46	5.33			
С	0.45	0.58	0.531			
D	6.00	6.20	6.10			
D1	5.21	-	-			
е	-	-	2.286			
Е	6.45	6.70	6.58			
E1	4.32	-	-			
H	9.40	10.41	9.91			
L	1.40	1.78	1.59			
L3	0.88	1.27	1.08			
L4	0.64	1.02	0.83			
а	0°	10°	-			
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Υ	2.600		
Y1	5.700		
Y2	10.700		



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